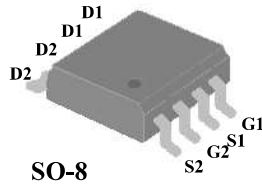


# AP4812

## N-Channel Power MOSFET

- ▼ Lower Gate Charge
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free

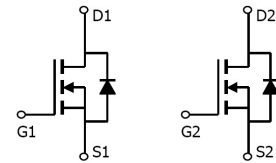


$BV_{DSS}$	30V
$R_{DS(ON)}$	15m $\Omega$
$I_D$	8A

### Description

AP4812 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SO-8 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.



### Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_A=25^\circ\text{C}$	Drain Current, $V_{GS} @ 10V^3$	8	A
$I_D@T_A=70^\circ\text{C}$	Drain Current, $V_{GS} @ 10V^3$	5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	30	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2.5	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	50	$^\circ\text{C}/\text{W}$

## N-Channel Power MOSFET

Electrical Characteristics@ $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=8A$		15	20	$m\Omega$
		$V_{GS}=4.5V, I_D=6A$		20	26	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2.5	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=8A$		15		S
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V$	-	-	10	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge	$I_D=8A$		4.1		nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=15V$	-	1.1	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	2.5	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V$	-	8	-	ns
$t_r$	Rise Time	$I_D=1A$	-	7	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	15	-	ns
$t_f$	Fall Time	$R_D=15\Omega$	-	5	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	350	420	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	55	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	35	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	3.2	-	$\Omega$

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=1.1A, V_{GS}=0V$	-	-	1.0	V
$t_{rr}$	Reverse Recovery Time	$I_S=8A, V_{GS}=0V,$	-	15	-	ns
$Q_{rr}$	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	14	-	nC

## Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board,  $t \leq 10\text{sec}$  ;  $125^{\circ}\text{C}/\text{W}$  when mounted on Min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

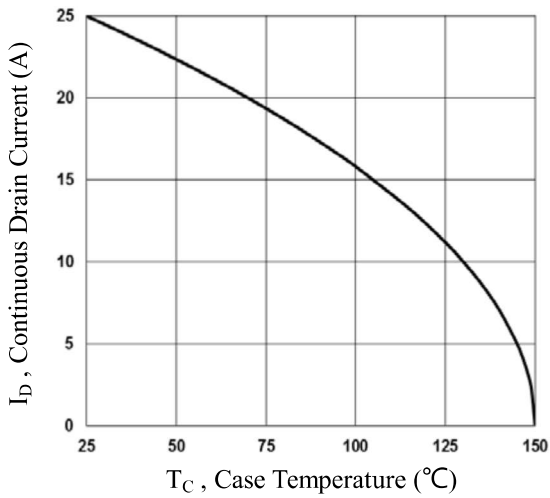
USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

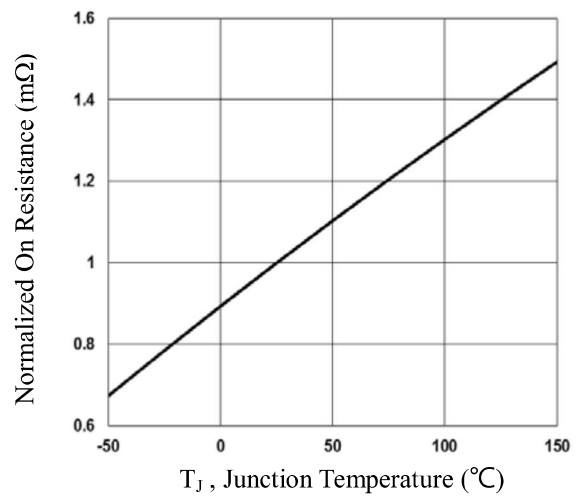
APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

**AP4812**

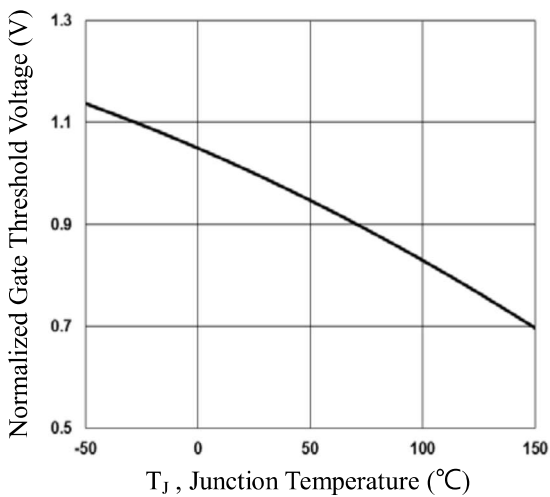
**N-Channel Power MOSFET**



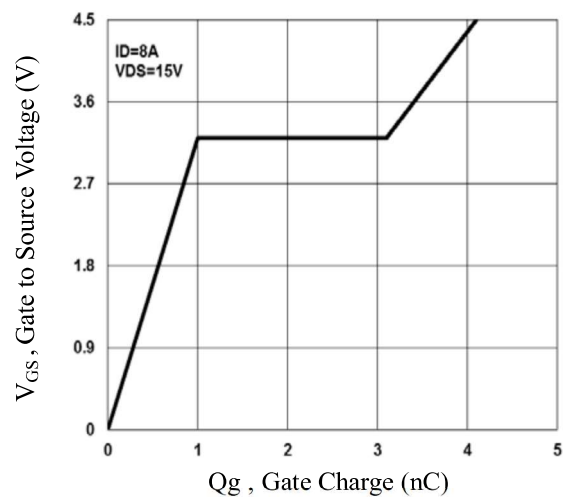
**Fig.1 Continuous Drain Current vs.  $T_C$**



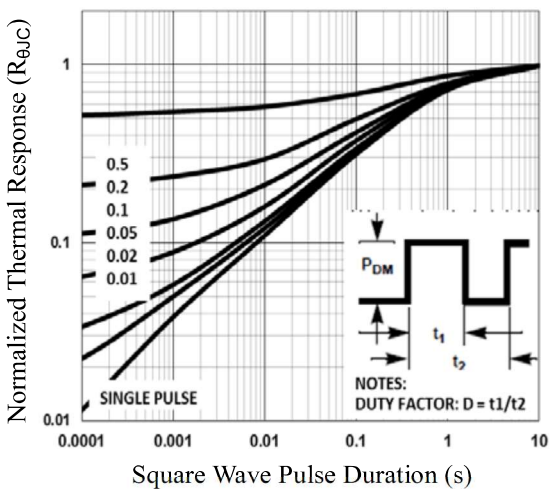
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$**



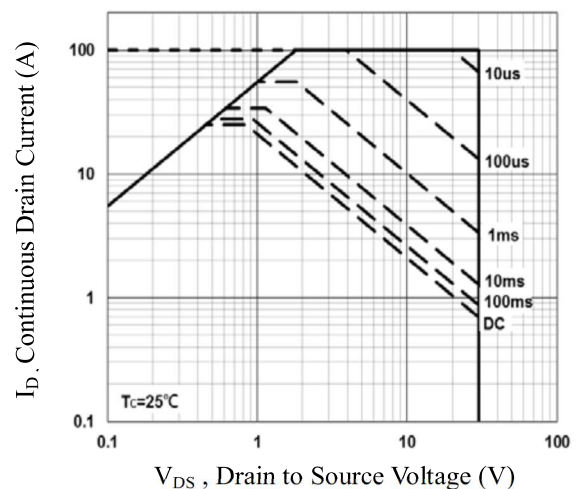
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



**Fig.4 Gate Charge Waveform**



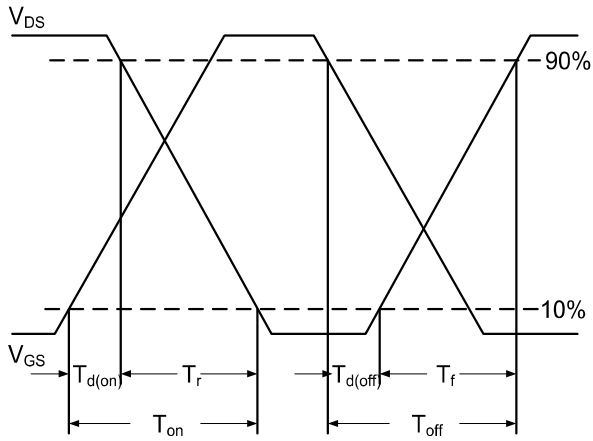
**Fig.5 Normalized Transient Response**



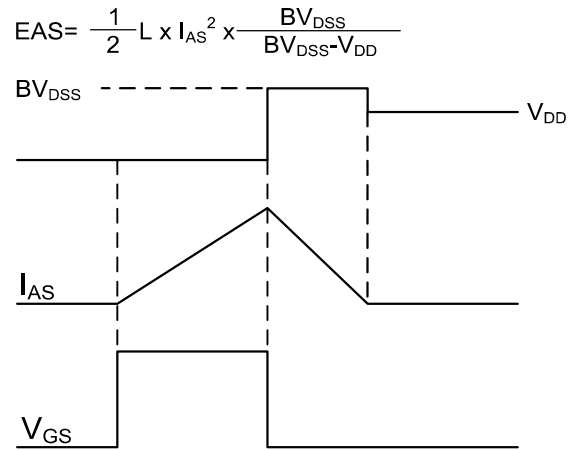
**Fig.6 Maximum Safe Operation Area**

**AP4812**

**N-Channel Power MOSFET**



**Fig.7 Switching Time Waveform**



**Fig.8 EAS Waveform**

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Quan Li](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#)  
[IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [SQM120N06-3M5L-GE3](#) [TK31J60W5,S1VQ\(O](#) [TK31J60W,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#)  
[2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)  
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)  
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)  
[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [PJMF280N65E1\\_T0\\_00201](#) [PJMF380N65E1\\_T0\\_00201](#) [PJMF280N60E1\\_T0\\_00201](#)  
[PJMF600N65E1\\_T0\\_00201](#) [PJMF900N65E1\\_T0\\_00201](#) [PJMF900N60E1\\_T0\\_00201](#)